

SPEC SHEET (FOR REFERENCE)	SHEET No.	G05046A	Page.
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TYPE : 6PT2302N1T**

CHIP SIZE	0.56 * 0.43 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	64,000 pcs

Maximum Ratings(Ta=25°C)

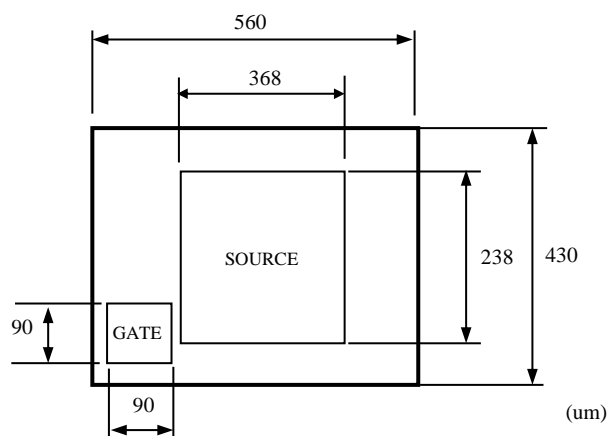
Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	20	V
Gate-source voltage	VGSS	±8	V
Drain Current (DC)	ID	0.95	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±3	uA	VGS=±8.0V VDS=0V
2	IDSS			500	nA	VDS=20.0V VGS=0V
3	BVDSS	23			V	ID=250uA
4	VTH	0.53		1.1	V	ID=250uA
5	Ron 1		0.14	0.23	Ω	ID=600mA VGS=4.5V
6	Ron 2		0.2	0.275	Ω	ID=500mA VGS=2.5V
7	Ron 3		0.3	0.7	Ω	ID=350mA VGS=1.8V
8	Ron 4		0.5	9.5	Ω	ID=40mA VGS=1.5V
9	VSD			1.1	V	IS=200mA

※ Built-in ZD between Gate and Source.



TENTATIVE

NOTE: